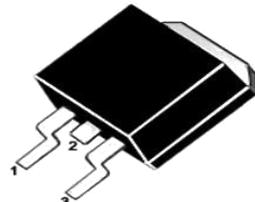
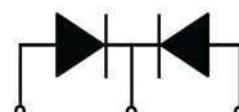


<p>MUR1610CT-MUR1660CT</p> <p>Features:</p> <ul style="list-style-type: none"> <input type="checkbox"/> High surge capacity <input type="checkbox"/> Low Forward Voltage Drop. <input type="checkbox"/> High Current Capability. <input type="checkbox"/> Super Fast Switching Speed For High Efficiency 	 TO-263  
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Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	MUR 1610 CT	MUR 1615 CT	MUR 1620 CT	MUR 1640 CT	MUR 1660 CT	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	100	150	200	400	600	V
Working Peak Reverse Voltage	V _{RWM}	70	105	140	280	420	V
DC Blocking Voltage	V _{R(DC)}	100	150	200	400	600	V
Average Rectified Forward Current Per Leg Total Device	I _{F(AV)}			8 16			A
Peak Rectified Forward Current Per Diode Leg	I _{FM}			16			A
Nonrepetitive Peak Surge Current(Surge applied at rated load conditions half wave, single phase, 60 Hz)	I _{FSM}			180			A
Operating Junction Temperature and Storage Temperature	T _J , T _{Stg}		1. Anode 2. Cathode -55 to +150	3. Anode			°C
Maximum Thermal Resistance, Junction-to-Case(Per Leg)	R _{θJC}		3.0		2.0		°C/ W

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Parameter	Symbol	MUR 1610 CT	MUR 1615 CT	MUR 1620 CT	MUR 1640 CT	MUR 1660 CT	Unit
Forward Voltage (Note 1)(I _F = 8.0 A, T _C = 25°C)	V _F		1.0		1.3	1.7	V
Maximum Instantaneous Reverse Current (Note 1) (Rated DC Voltage, T _C = 150°C) (Rated DC Voltage, T _C = 25°C)	I _R		250 10		500 10		μ A
Maximum Reverse Recovery Time (I _F = 0.5 A, I _R = 1.0 A, I _{REC} = 0.25 A)	T _{RR}		35		35		ns

Note 1.Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2.0%

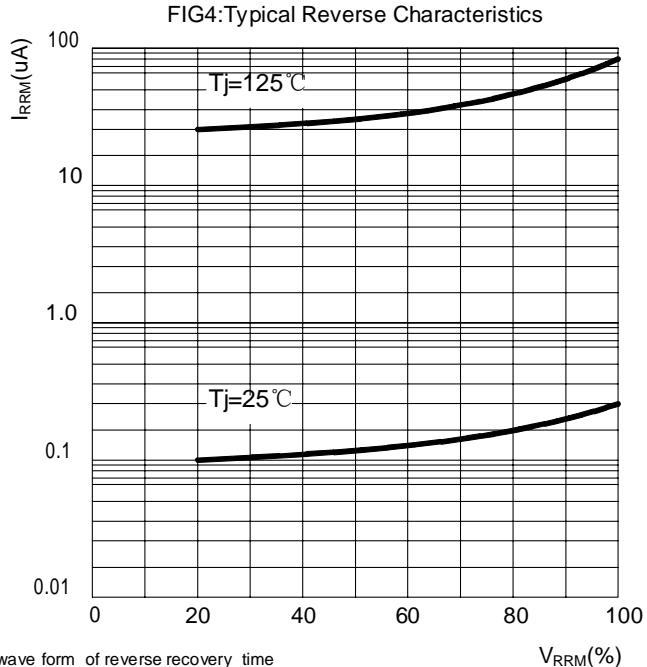
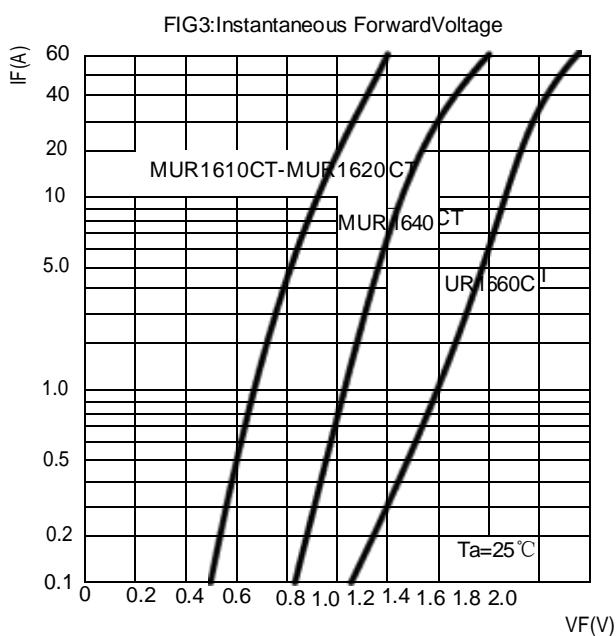
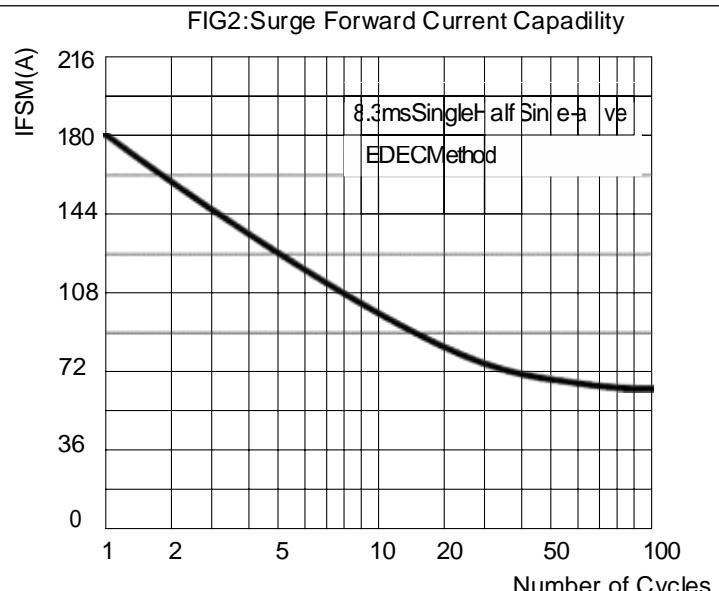
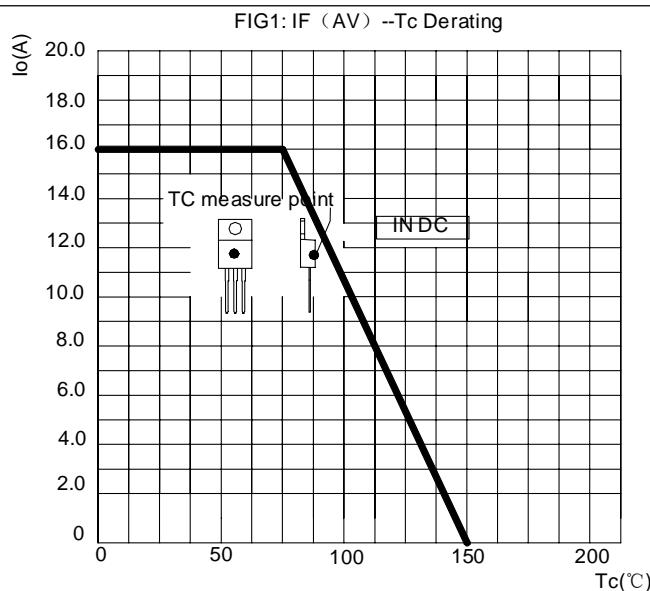
Typical Characteristics

FIG.5: Diagram of circuit and Testing wave form of reverse recovery time

